# **Hex Unbuffered Inverter**

# High-Performance Silicon-Gate CMOS

The MC74HCU04A is identical in pinout to the LS04 and the MC14069UB. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of six single-stage inverters. These inverters are well suited for use as oscillators, pulse shapers, and in many other applications requiring a high-input impedance amplifier. For digital applications, the HC04A is recommended.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V; 2.5 to 6.0 V in Oscillator Configurations
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 12 FETs or 3 Equivalent Gates
- Pb-Free Packages are Available



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MARKING DIAGRAMS



PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A

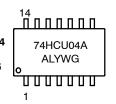




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

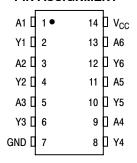
L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

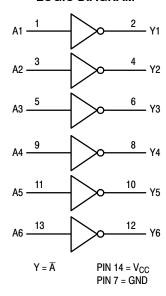
## **PIN ASSIGNMENT**



## **FUNCTION TABLE**

Inputs	Outputs	
A	Y	
L H	H	

## **LOGIC DIAGRAM**



## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCU04AN	PDIP-14	
MC74HCU04ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HCU04AD	SOIC-14	
MC74HCU04ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HCU04ADR2	SOIC-14	
MC74HCU04ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HCU04ADTR2	TSSOP-14*	•
MC74HCU04ADTR2G	TSSOP-14*	
MC74HCU04AFEL	SOEIAJ-14	
MC74HCU04AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±[ <b>2</b> 0	mA
l <sub>out</sub>	DC Output Current, per Pin	±[ <b>2</b> 5	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±[\$0	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: -10mW/°C from 65° to 125°C

SOIC Package: -7mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	<b>– 55</b>	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	-	No Limit	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.5 \text{ V*}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.7 2.5 3.6 4.8	1.7 2.5 3.6 4.8	1.7 2.5 3.6 4.8	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = V_{CC} - 0.5 V^*$ $ I_{out}  \le 20 \mu A$	2.0 3.0 4.5 6.0	0.3 0.5 0.8 1.1	0.3 0.5 0.8 1.1	0.3 0.5 0.8 1.1	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = GND$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	1.8 4.0 5.5	1.8 4.0 5.5	1.8 4.0 5.5	V
		$\begin{tabular}{ll} $V_{in} = GND$ & $ I_{out}  \le 2.4 \text{ mA}$ \\ $ I_{out}  \le 4.0 \text{ mA}$ \\ $ I_{out}  \le 5.2 \text{ mA}$ \\ \end{tabular}$	3.0 4.5 6.0	2.36 3.86 5.36	2.26 3.76 5.26	2.20 3.70 5.20	

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu		uaranteed Limit		
Symbol	Parameter	Test Conditions	V <sub>C</sub>		– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{CC}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	5	0.2 0.5 0.5	0.2 0.5 0.5	0.2 0.5 0.5	V
		$\begin{aligned} V_{in} = V_{CC} & &  I_{out}  \leq \\ &  I_{out}  \leq \\ &  I_{out}  \leq \end{aligned}$	4.0 mA 4.9	5	0.32 0.32 0.32	0.32 0.37 0.37	0.32 0.40 0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	0	±[0.1	±[1.0	±[1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	0	1	10	40	μΑ

<sup>1.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

			Gu	aranteed Li	mit	
Symbol	Parameter	v <sub>cc</sub> v	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	70 40 14 12	90 45 18 15	105 50 21 18	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF

<sup>3.</sup> For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>4.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Inverter)*	15	pF

Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

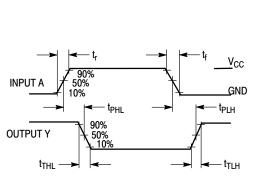
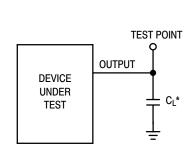


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

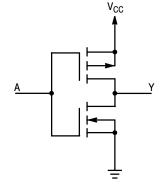


Figure 3. Logic Detail (1/6 of Device Shown)

<sup>2.</sup> For  $V_{CC} = 2.0 \text{ V}$ ,  $V_{out} = 0.2 \text{ V}$  or  $V_{CC} - 0.2 \text{ V}$ .

## **TYPICAL APPLICATIONS**

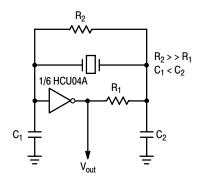


Figure 4. Crystal Oscillator

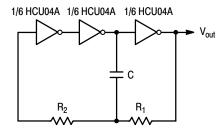


Figure 5. Stable RC Oscillator

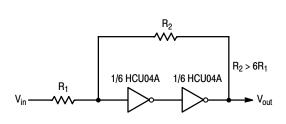


Figure 6. Schmitt Trigger

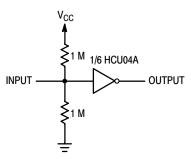


Figure 7. High Input Impedance Single-Stage Amplifier with a 2 to 6 V Supply Range

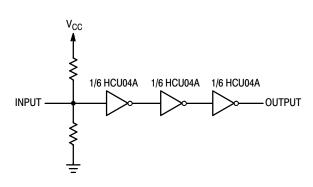
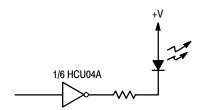


Figure 8. Multi-Stage Amplifier

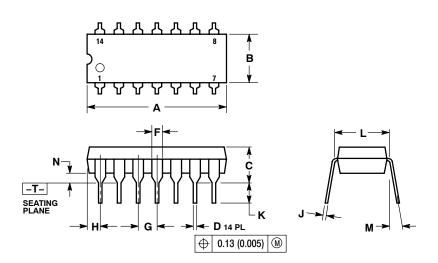


For reduced power supply current, use high-efficiency LEDs such as the Hewlett-Packard HLMP series or equivalent.

Figure 9. LED Driver

## **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 ISSUE P

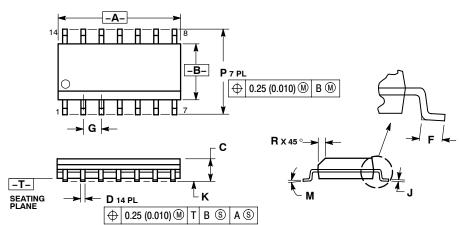


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
Κ	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38	1.01

## **PACKAGE DIMENSIONS**

SOIC-14 CASE 751A-03 **ISSUE H** 



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

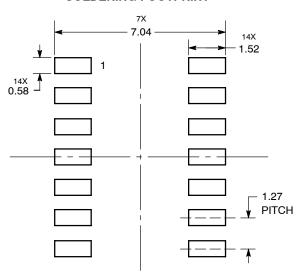
  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PEH SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0°	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

## **SOLDERING FOOTPRINT\***

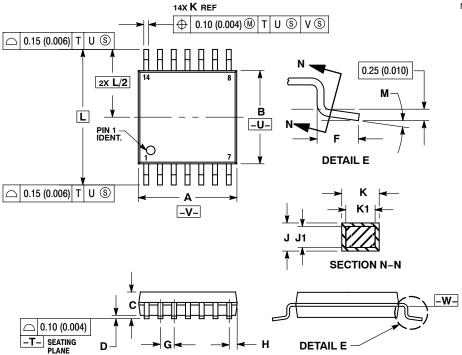


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

## TSSOP-14 CASE 948G-01 **ISSUE B**

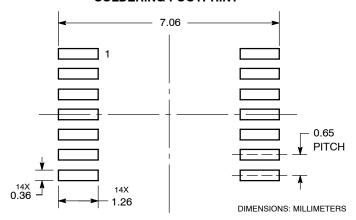


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER

  - DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
     CONTROLLING DIMENSION: MILLIMETER.
     DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
     DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  - NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE
    DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
    7. DIMENSION A AND B ARE TO BE PETERMINED AT DATUM PLANE—W.

$\theta$	HANAINII	<del>) AI I)A</del>	HUM PL	<del>^\\</del> -\\	
	MILLIMETERS		TERS INCHE		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
М	0 °	8 °	0 °	8 °	

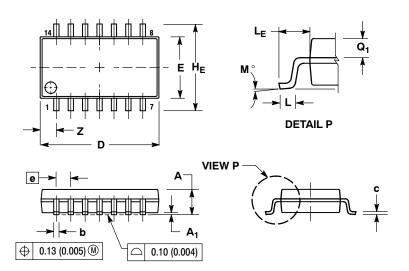
## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 **ISSUE A** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	) BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		1.42		0.056

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